



DISCRETE POWER DIODES and THYRISTORS
DATA BOOK



ST203C..C SERIES

INVERTER GRADE THYRISTORS

Hockey Puk Version

Features

- Metal case with ceramic insulator
- International standard case TO-200AB (A-PUK)
- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- High surge current capability
- Low thermal impedance
- High speed performance

370A

Typical Applications

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters



case style TO-200AB (A-PUK)

Major Ratings and Characteristics

Parameters	ST203C..C	Units
$I_{T(AV)}$	370	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	700	A
@ T_{hs}	25	°C
I_{TSM}	5260	A
@ 50Hz	5260	A
@ 60Hz	5510	A
I^2t	138	KA ² s
@ 50Hz	138	KA ² s
@ 60Hz	126	KA ² s
V_{DRM}/V_{RRM}	1000 to 1200	V
t_q range	20 to 30	μs
T_J	- 40 to 125	°C

ST203C..C Series

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , maximum repetitive peak voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_{J\max}$ mA
ST203C..C	10	1000	1100	40
	12	1200	1300	

Current Carrying Capability

Frequency				Units	
50Hz	860	750	1340	1160	A
400Hz	840	706	1400	1220	
1000Hz	700	580	1350	1170	
2500Hz	430	340	980	830	
Recovery voltage V_r	50	50	50	50	
Voltage before turn-on V_d	V_{DRM}		V_{DRM}		V
Rise of on-state current di/dt	50	50	-	-	A/ μ s
Heatsink temperature	40	55	40	55	°C
Equivalent values for RC circuit	$47\Omega / 0.22\mu F$		$47\Omega / 0.22\mu F$		

On-state Conduction

Parameter	ST203C..C	Units	Conditions					
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	370 (140)	A	180° conduction, half sine wave double side (single side) cooled					
	55 (85)	°C						
$I_{T(RMS)}$ Max. RMS on-state current	700	A	DC @ 25°C heatsink temperature double side cooled					
I_{TSM} Max. peak, one half cycle, non-repetitive surge current	5260		$t = 10ms$	No voltage reapplied	Sinusoidal half wave, Initial $T_J = T_{J\max}$			
	5510							
	4420		$t = 8.3ms$	100% V_{RRM} reapplied				
	4630							
I^2t Maximum I^2t for fusing	138	KA ² s	$t = 10ms$	No voltage reapplied				
	126							
	98		$t = 8.3ms$	100% V_{RRM} reapplied				
	89							
$I^{2\sqrt{t}}$ Maximum $I^{2\sqrt{t}}$ for fusing	1380	KA ² /s	$t = 0.1$ to $10ms$, no voltage reapplied					

ST203C..C Series

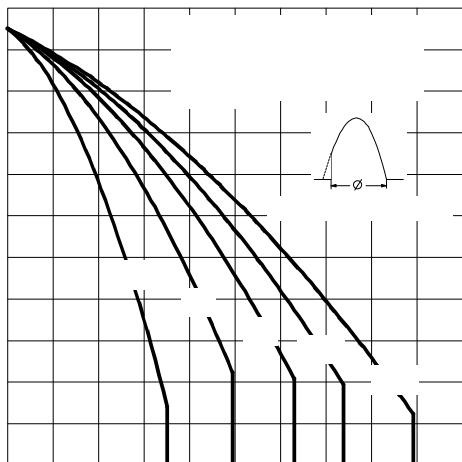


Fig. 3 - Current Ratings Characteristics

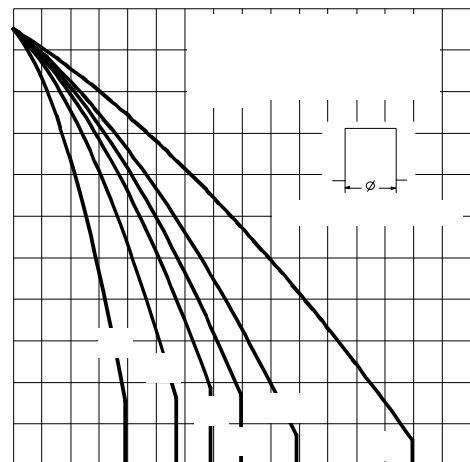


Fig. 4 - Current Ratings Characteristics

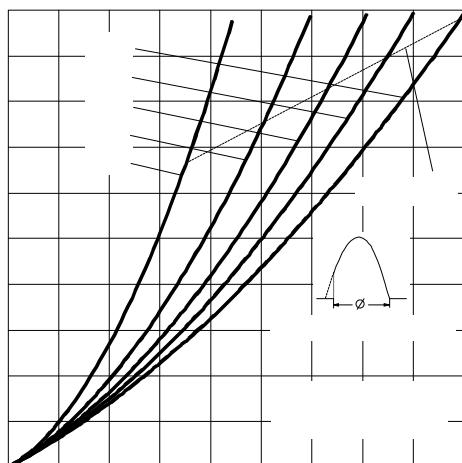


Fig. 5 - On-state Power Loss Characteristics

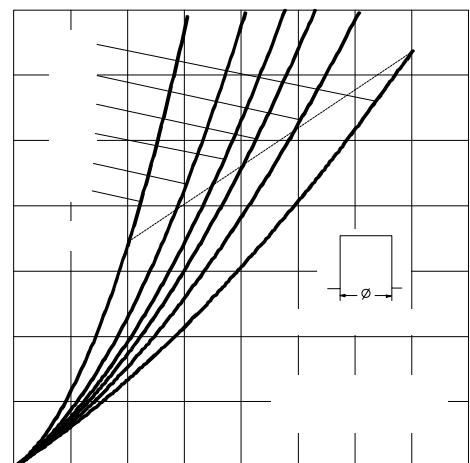


Fig. 6 - On-state Power Loss Characteristics

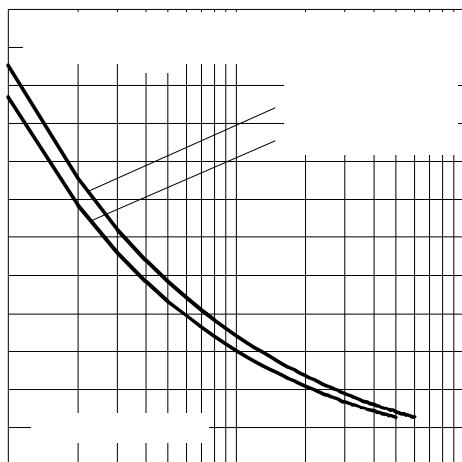


Fig. 7 - Maximum Non-repetitive Surge Current

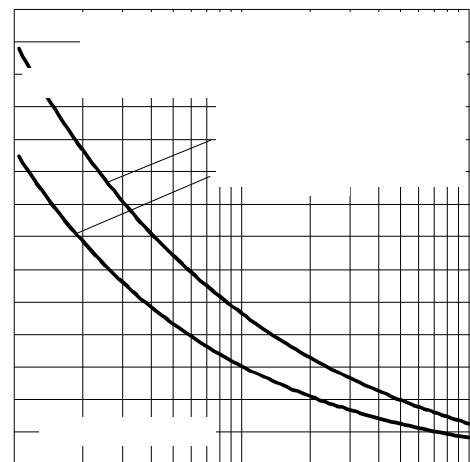


Fig. 8 - Maximum Non-repetitive Surge Current

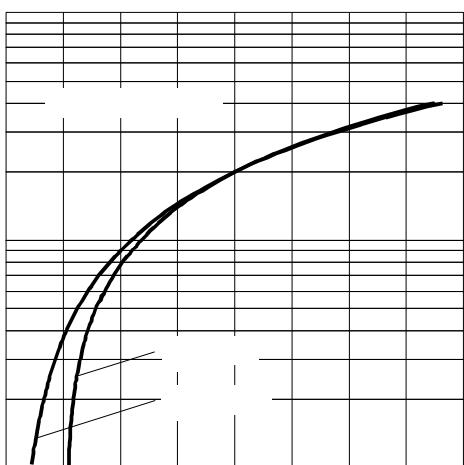


Fig. 9 - On-state Voltage Drop Characteristics

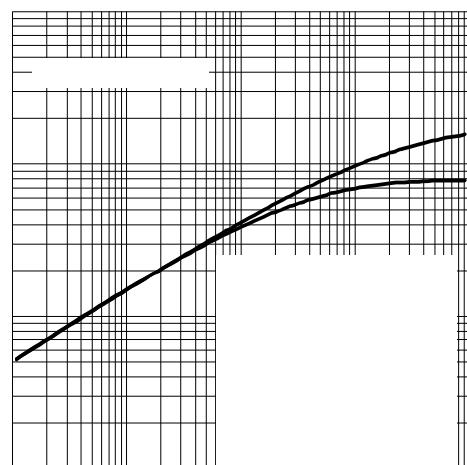


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

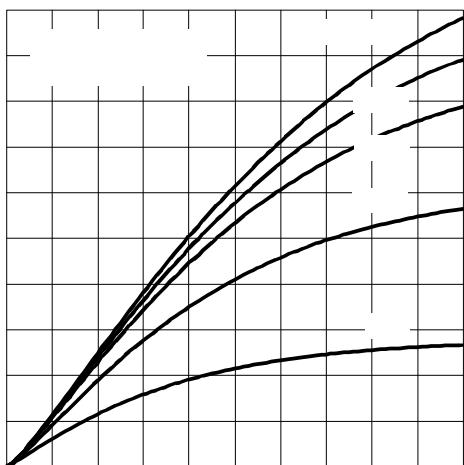


Fig. 11 - Reverse Recovered Charge Characteristics

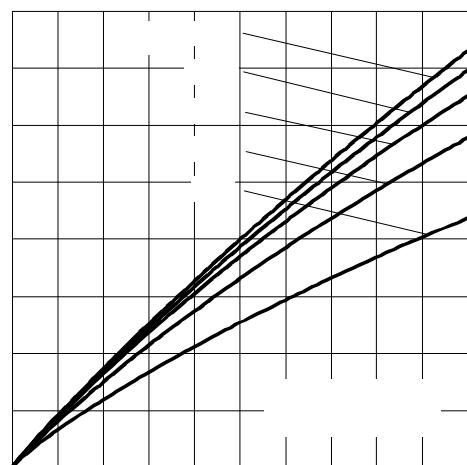


Fig. 12 - Reverse Recovery Current Characteristics

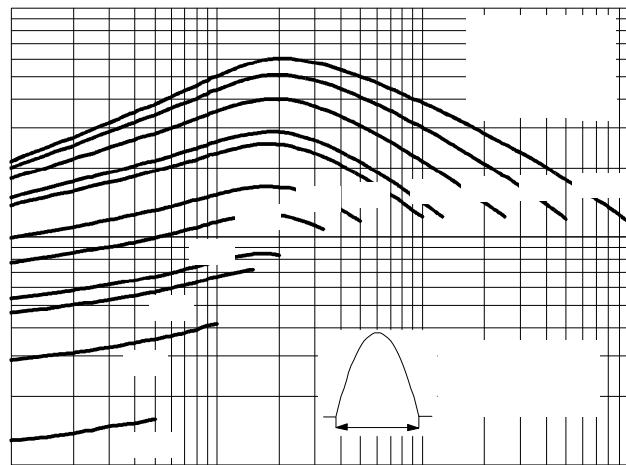
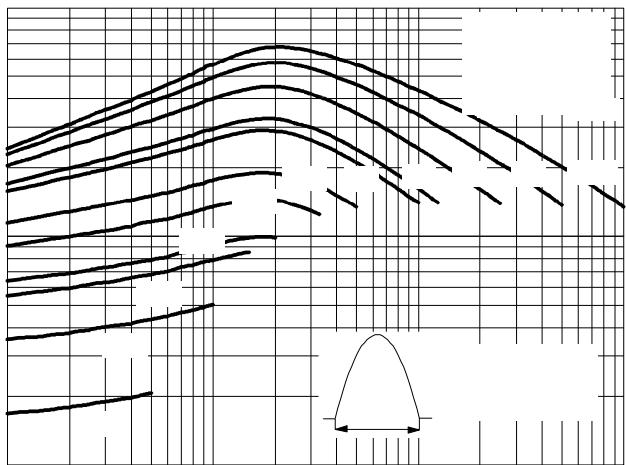


Fig. 13 - Frequency Characteristics

ST203C..C Series

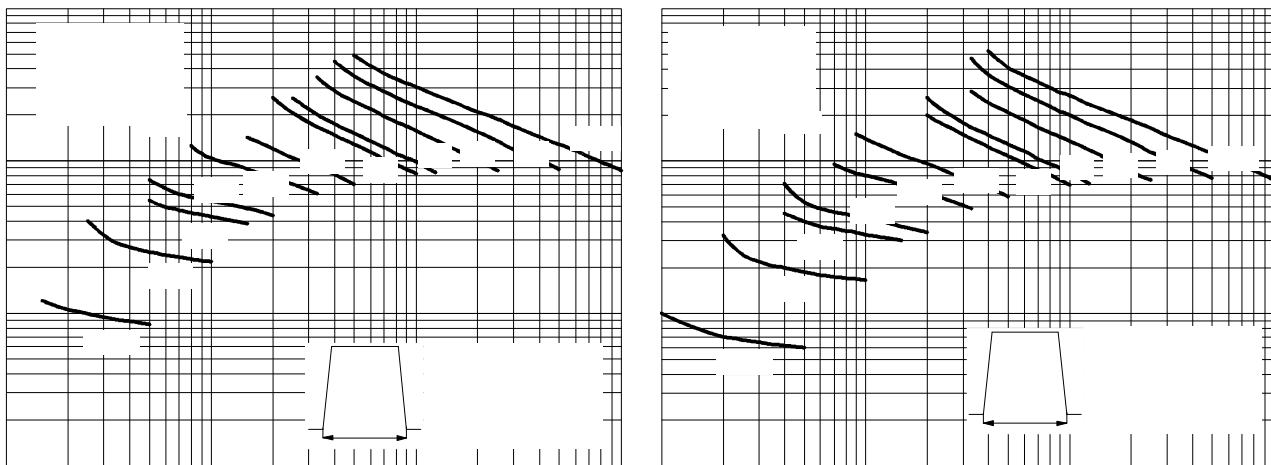


Fig. 14 - Frequency Characteristics

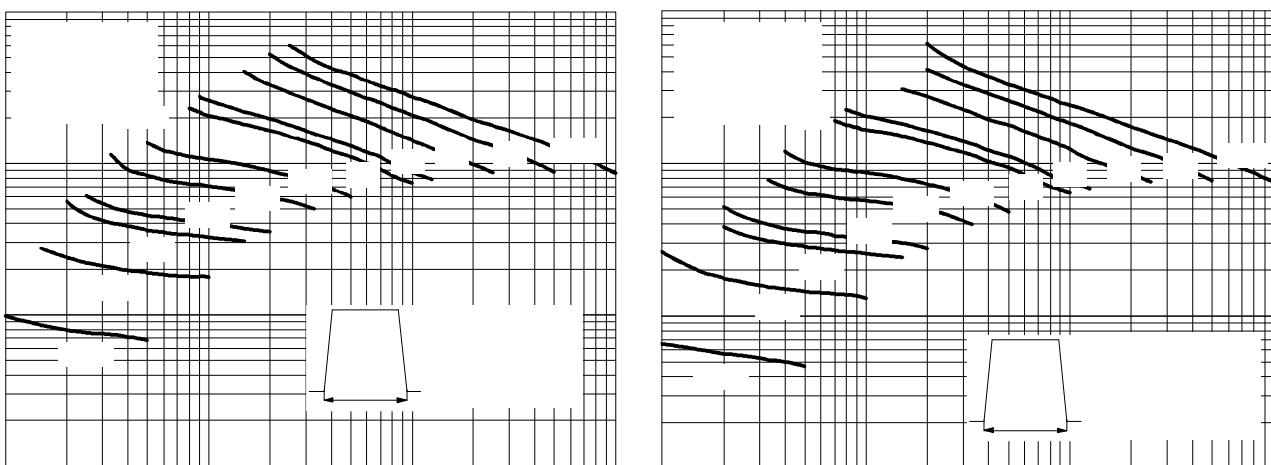


Fig. 15 - Frequency Characteristics

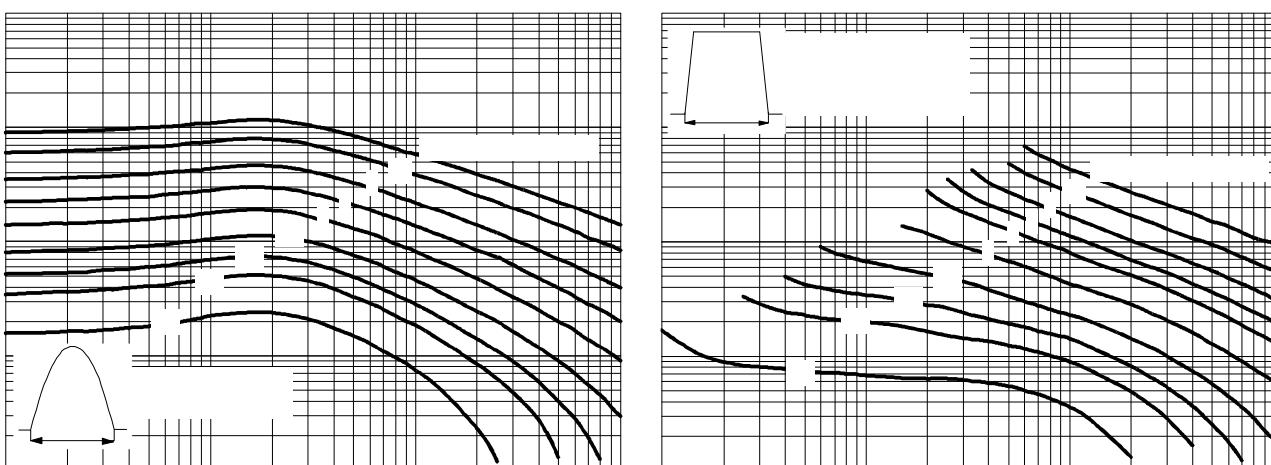


Fig. 16 - Maximum On-state Energy Power Loss Characteristics

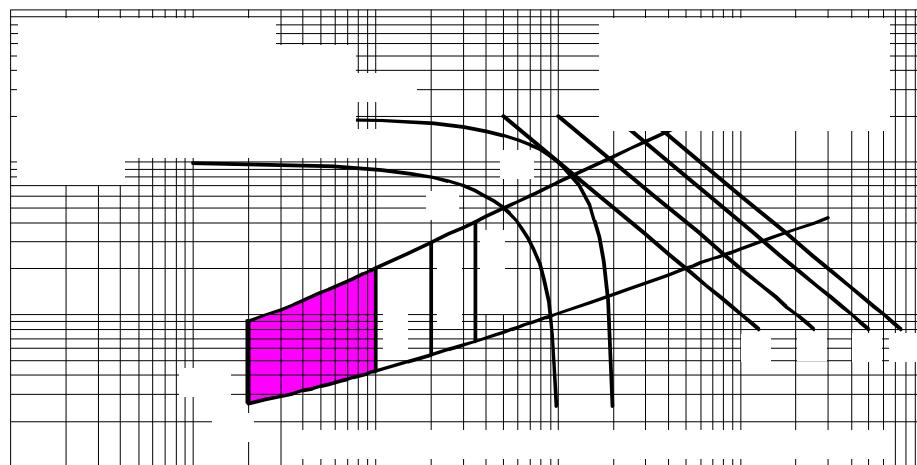


Fig. 17 - Gate Characteristics

On-state Conduction

Parameter	ST203C..C	Units	Conditions
V_{TM}	Max. peak on-state voltage	V	$I_{TM} = 600A, T_J = T_J \text{ max}, t_p = 10\text{ms sine wave pulse}$
$V_{T(TO)1}$	Low level value of threshold voltage		$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}, T_J = T_J \text{ max.})$
$V_{T(TO)2}$	High level value of threshold voltage		$(I > \pi \times I_{T(AV)}, T_J = T_J \text{ max.})$
r_{t1}	Low level value of forward slope resistance	$\text{m}\Omega$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}, T_J = T_J \text{ max.})$
r_{t2}	High level value of forward slope resistance		$(I > \pi \times I_{T(AV)}, T_J = T_J \text{ max.})$
I_H	Maximum holding current	mA	$T_J = 25^\circ\text{C}, I_T > 30\text{A}$
I_L	Typical latching current		$T_J = 25^\circ\text{C}, V_A = 12\text{V}, R_a = 6\Omega, I_G = 1\text{A}$

Switching

Parameter	ST203C..C	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	A/ μ s	$T_J = T_J \text{ max.}, V_{DRM} = \text{rated } V_{DRM}$ $I_{TM} = 2 \times di/dt$
t_d	Typical delay time	μ s	$T_J = 25^\circ\text{C}, V_{DM} = \text{rated } V_{DRM}, I_{TM} = 50\text{A DC}, t_p = 1\mu\text{s}$ Resistive load, Gate pulse: 10V, 5Ω source
t_q	Max. turn-off time		$T_J = T_J \text{ max.}, I_{TM} = 300\text{A}, \text{commutating } di/dt = 20\text{A}/\mu\text{s}$ $V_R = 50\text{V}, t_p = 500\mu\text{s}, dv/dt: \text{see table in device code}$

Blocking

Parameter	ST203C..C	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	V/ μ s	$T_J = T_J \text{ max. linear to 80\% } V_{DRM}$, higher value available on request
I_{RRM} I_{DRM}	Max. peak reverse and off-state leakage current	mA	$T_J = T_J \text{ max.}, \text{rated } V_{DRM}/V_{RRM} \text{ applied}$

Triggering

Parameter	ST203C..C	Units	Conditions
P_{GM}	Maximum peak gate power	W	$T_J = T_J \text{ max.}, f = 50\text{Hz}, d\% = 50$
$P_{G(AV)}$	Maximum average gate power		
I_{GM}	Max. peak positive gate current	A	$T_J = T_J \text{ max.}, t_p \leq 5\text{ms}$
$+V_{GM}$	Maximum peak positive gate voltage		
$-V_{GM}$	Maximum peak negative gate voltage	V	$T_J = T_J \text{ max.}, t_p \leq 5\text{ms}$
I_{GT}	Max. DC gate current required to trigger	mA	$T_J = 25^\circ\text{C}, V_A = 12\text{V}, R_a = 6\Omega$
V_{GT}	Max. DC gate voltage required to trigger		
I_{GD}	Max. DC gate current not to trigger	mA	$T_J = T_J \text{ max.}, \text{rated } V_{DRM} \text{ applied}$
V_{GD}	Max. DC gate voltage not to trigger		

ST203C..C Series

Thermal and Mechanical Specification

Parameter	ST203C..C	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	°C
T_{stg}	Max. storage temperature range	-40 to 150	
R_{thJ-hs}	Max. thermal resistance, junction to heatsink	0.17 0.08	K/W
R_{thC-hs}	Max. thermal resistance, case to heatsink	0.033 0.017	
F	Mounting force, $\pm 10\%$	4900 (500)	N (Kg)
wt	Approximate weight	50	g
Case style	TO - 200AB (A-PUK)	See Outline Table	

ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.015	0.017	0.011	0.011	K/W	$T_J = T_{J \text{ max.}}$
120°	0.018	0.019	0.019	0.019		
90°	0.024	0.024	0.026	0.026		
60°	0.035	0.035	0.036	0.037		
30°	0.060	0.060	0.060	0.061		

Ordering Information Table

Device Code	ST	20	3	C	12	C	H	H	1	
	1	2	3	4	5	6	7	8	9	10
1	- Thyristor									
2	- Essential part number									
3	- 3 = Fast turn off									
4	- C = Ceramic Puk									
5	- Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)									
6	- C = Puk Case TO-200AB (A-PUK)									
7	- Reapplied dv/dt code (for t_q test condition)									
8	- t_q code _____									
9	- 0 = Eyelet term. (Gate and Aux. Cathode Unsoldered Leads) 1 = Fast-on term. (Gate and Aux. Cathode Unsoldered Leads) 2 = Eyelet term. (Gate and Aux. Cathode Soldered Leads) 3 = Fast-on term. (Gate and Aux. Cathode Soldered Leads)									
10	- Critical dv/dt: None = 500V/ μ sec (Standard value) L = 1000V/ μ sec (Special selection)									

dv/dt - t_q combinations available					
dv/dt (V/ μ s)	20	50	100	200	400
t_q (μ s)	20	CK	DK	EK	--
	25	CJ	DJ	EJ	FJ *
	30	CH	DH	EH	HH

*Standard part number.
All other types available only on request.

Outline Table

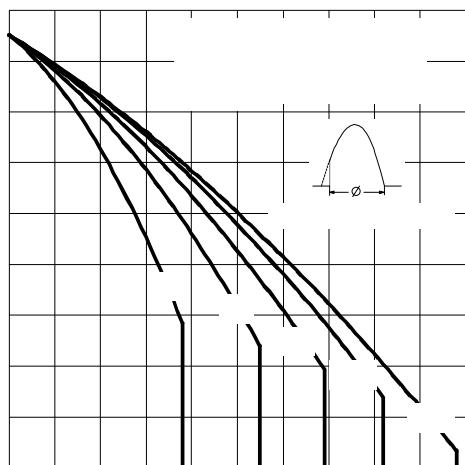
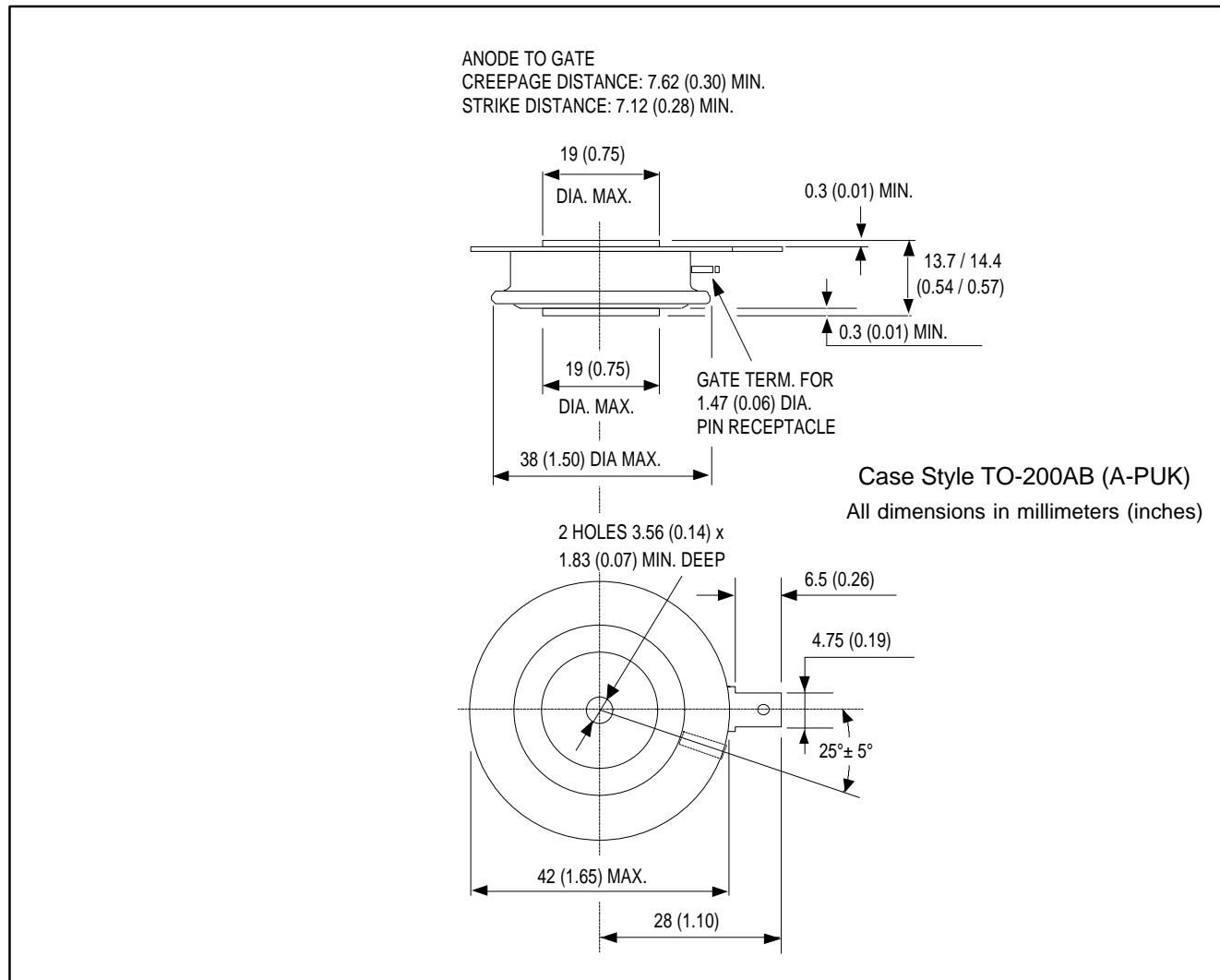


Fig. 1 - Current Ratings Characteristics

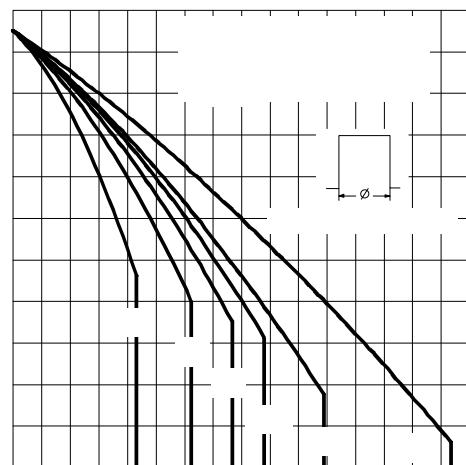


Fig. 2 - Current Ratings Characteristics